

## Product Overview

### NGTB15N120FL2: IGBT 1200V 15A SOLAR/UPS

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

### Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 10 s Short Circuit Capability
- These are Pb-Free Devices

### Applications

- Solar Inverter
- Uninterruptible Power Inverter Supplies (UPS)
- Welding

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	$V_{(BR)CES}$ Typ (V)	$I_C$ Max (A)	$V_{CE(s)at}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_{rr}$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand ( $\mu$ s)	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co-Packaged Diode	Package Type
NGTB15N120FL2WG	2.1599	Pb-free Halide free non AEC-Q and PPAP	Active	1200	15	2	2	0.37	1.2	110	11	109	10	-	294	Yes	TO-247-3

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